

Abstract Of The Disclosure

Additional variants of the method of etching structures into an etching body, in particular recesses in a silicon body that are laterally defined in a precise manner by an etching mask, using a plasma, is described. In addition, the use of this method in the introduction of structures, in particular trenches having a high aspect ratio, into a dielectric layer or a dielectric base body and in a layer of silicon is described, isotropic underetching and/or isotropic, sacrificial-layer etching, in particular using fluorine radicals or a highly oxidizing fluorine compound such as ClF_3 , being performed after the production of the structures in at least some areas in the case of the layer made of silicon.